

## Midterm III

### Information that will be provided with the exam

Permittivity of free space  $\epsilon_0 = 8.85 \times 10^{-14} \text{ F/cm} = 8.85 \times 10^{-12} \text{ F/m}$

Element of charge  $q = 1.6 \times 10^{-19} \text{ C}$

1 Coulomb is equivalent to  $6.25 \times 10^{18}$  charges.

Charge on an electron is  $-q$

Relative permittivity (or relative dielectric constant) values for Si,  $\text{SiO}_2$

Avagadro's number:  $6.02 \times 10^{23}$

Statement that if an element has an atomic weight of A, then A grams of that element will have  $6.02 \times 10^{23}$  atoms.

Saturation velocity for electrons in silicon:  $10^7 \text{ cm/s}$

$n_i$  (intrinsic carrier concentration in silicon at 300 K) =  $10^{10} \text{ cm}^{-3}$

### Conductivity ( $\sigma$ ) and Drift Current Density ( $J$ ) for electrons in Semiconductor:

$\sigma = qn\mu_n$  where  $n$  is the volume carrier density and  $\mu_n$  is the electron mobility. Similar expression for holes with  $p$  (volume hole concentration) instead of  $n$  and hole mobility  $\mu_p$  instead of  $\mu_n$

$J = \sigma E$ , where  $E$  is the electric field

### Parallel Plate Capacitor:

Capacitance per unit area =  $\frac{\epsilon_0 \epsilon_r}{t_{ox}}$  where  $t_{ox}$  is the dielectric thickness

### MOSFET Linear Region:

NMOS: When  $V_{DS} \leq V_{GS} - V_T$

$$I_D = \mu_n C_{ox} \frac{W}{L} \left( [V_{GS} - V_t] V_{DS} - \frac{v_{DS}^2}{2} \right)$$

PMOS: When  $|V_{DS}| \leq |V_{GS}| - |V_T|$

$$I_D = \mu_p C_{ox} \frac{W}{L} \left( [V_{GS} - V_t] V_{DS} - \frac{v_{DS}^2}{2} \right)$$

### Saturation Region:

NMOS: When  $V_{DS} > V_{GS} - V_T$

$$I_D = \frac{1}{2}(\mu_n C_{ox}) \left(\frac{W}{L}\right) (V_{GS} - V_t)^2$$

PMOS: When  $|V_{DS}| > |V_{GS}| - |V_T|$

$$I_D = \frac{1}{2}(\mu_p C_{ox}) \left(\frac{W}{L}\right) (V_{GS} - V_t)^2$$

### Small signal model parameters:

$$\text{Small signal transconductance } g_m = \frac{2I_D}{(V_{GS} - V_T)} = \sqrt{2\mu_n C_{ox} \left(\frac{W}{L}\right) I_D}$$

### Unit conversion:

1  $\mu\text{m} = 10^{-4}$  cm =  $10^{-6}$  m; 1 nm =  $10^{-7}$  cm =  $10^{-9}$  m; 1 pA =  $10^{-12}$  A; 1 fF =  $10^{-15}$  F

## PART III

$$\begin{aligned}\sin x &= \pm \cos(x \mp 90^\circ) \\ \cos x &= \pm \sin(x \pm 90^\circ) \\ \sin x &= -\sin(x \pm 180^\circ) \\ \cos x &= -\cos(x \pm 180^\circ) \\ \sin(-x) &= -\sin x \\ \cos(-x) &= \cos x\end{aligned}$$

$$-\tan^{-1}(x) = \tan^{-1}(-x)$$

$$\mathbf{z} = x + jy = |\mathbf{z}|e^{j\theta}$$

$$x = \Re(\mathbf{z}) = |\mathbf{z}| \cos \theta$$

$$y = \Im(\mathbf{z}) = |\mathbf{z}| \sin \theta$$

$$\text{Euler's Identity: } e^{j\theta} = \cos \theta + j \sin \theta$$

$$\mathbf{z}_1 = x_1 + jy_1$$

$$\mathbf{z}_2 = x_2 + jy_2$$

$$\mathbf{z}_1 = \mathbf{z}_2 \text{ iff } x_1 = x_2 \text{ and } y_1 = y_2$$

$$\mathbf{z}_1 + \mathbf{z}_2 = (x_1 + x_2) + j(y_1 + y_2)$$

$$\mathbf{z}_1 \mathbf{z}_2 = |\mathbf{z}_1| |\mathbf{z}_2| e^{j(\theta_1 + \theta_2)}$$

$$\frac{\mathbf{z}_1}{\mathbf{z}_2} = \frac{|\mathbf{z}_1|}{|\mathbf{z}_2|} e^{j(\theta_1 - \theta_2)}$$